

FIG. 2

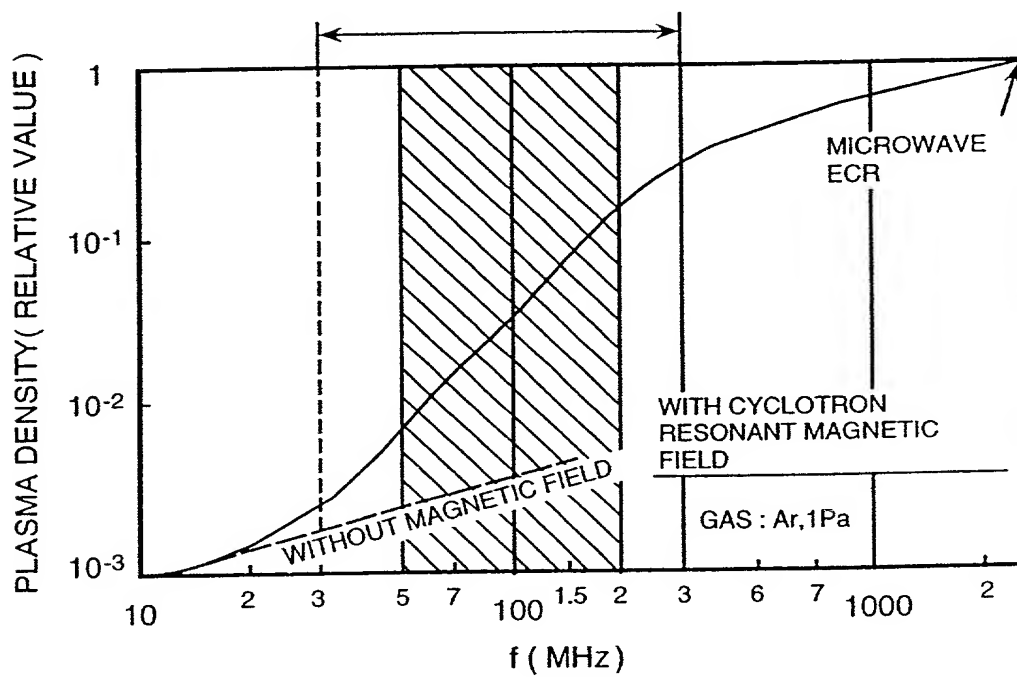
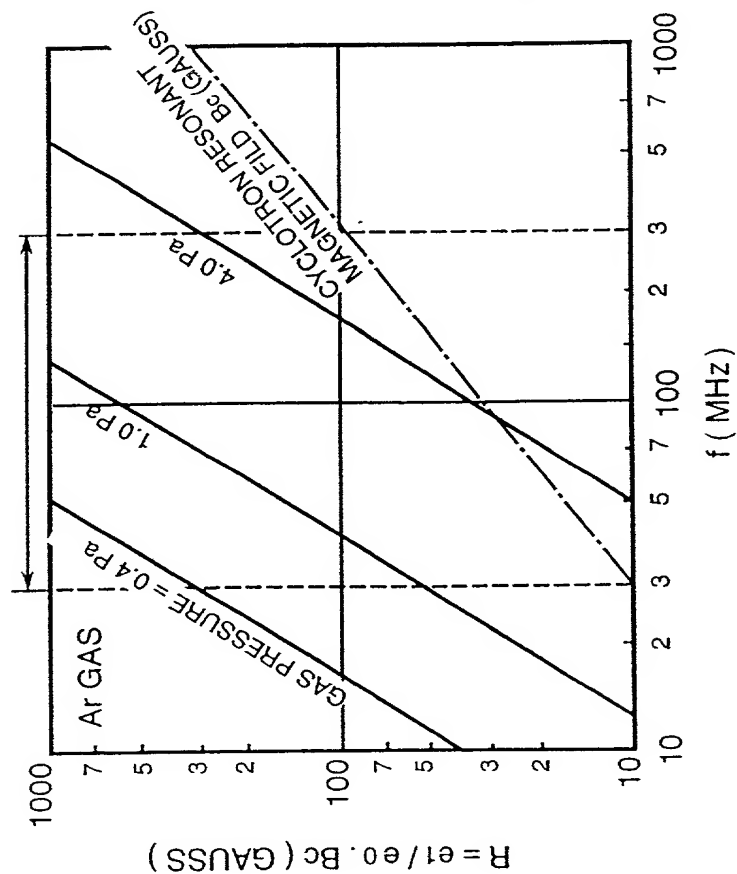


FIG. 3



$$B_c = 2 \pi f \cdot \frac{m}{e}$$

e_0 : ENERGY OBTAINED BY ELECTRON DURING ONE CYCLE OF RF UNDER CONDITION WITHOUT MAGNETIC FIELD

e_1 : ENERGY OBTAINED BY ELECTRON DURING ONE CYCLE OF RF UNDER CONDITION APPLIED WITH CYCLOTRON RESONANT MAGNETIC FIELD

FIG. 4

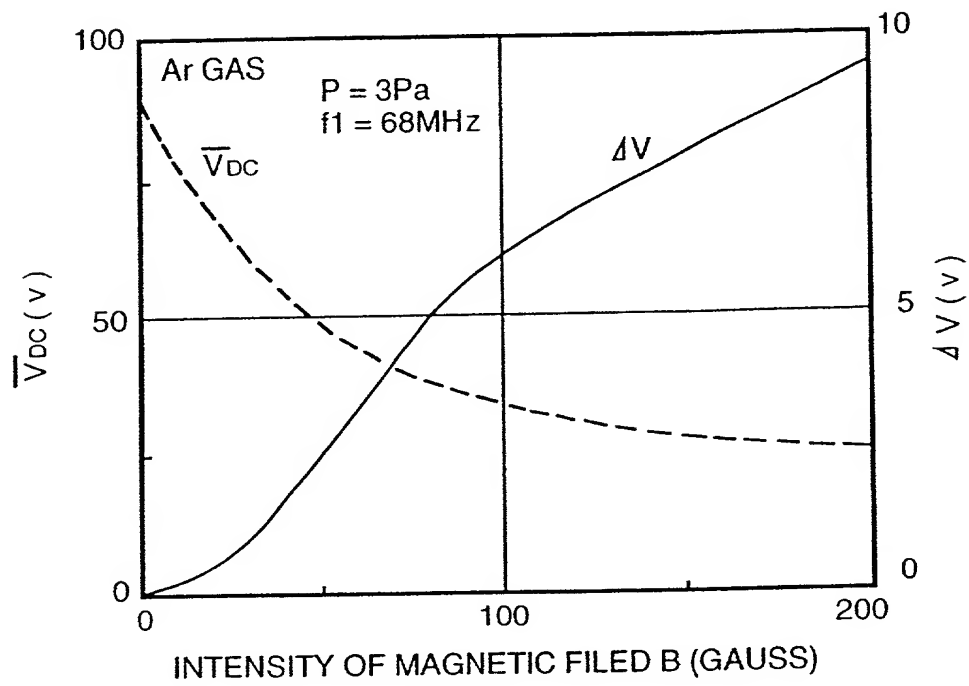


FIG. 5

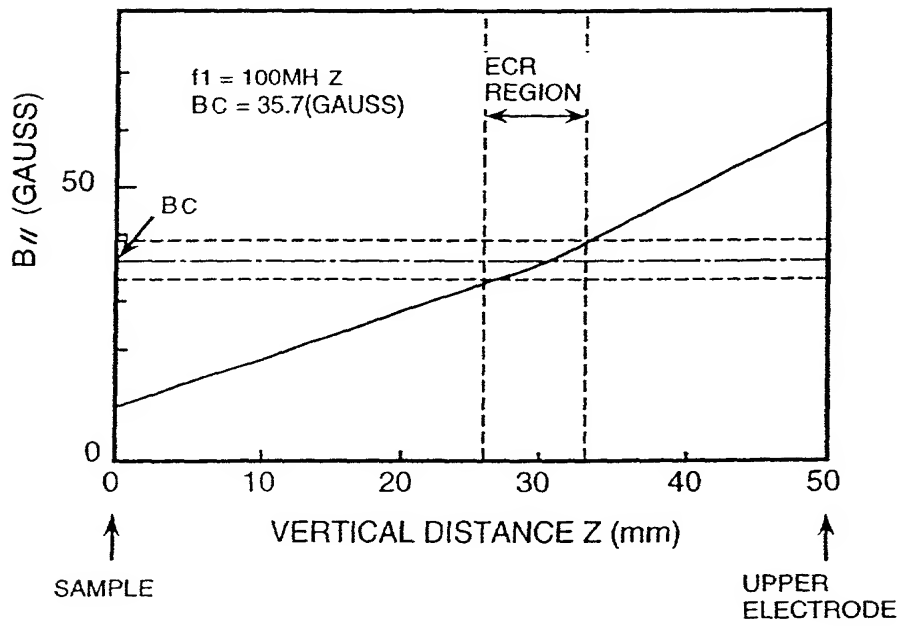


FIG. 6

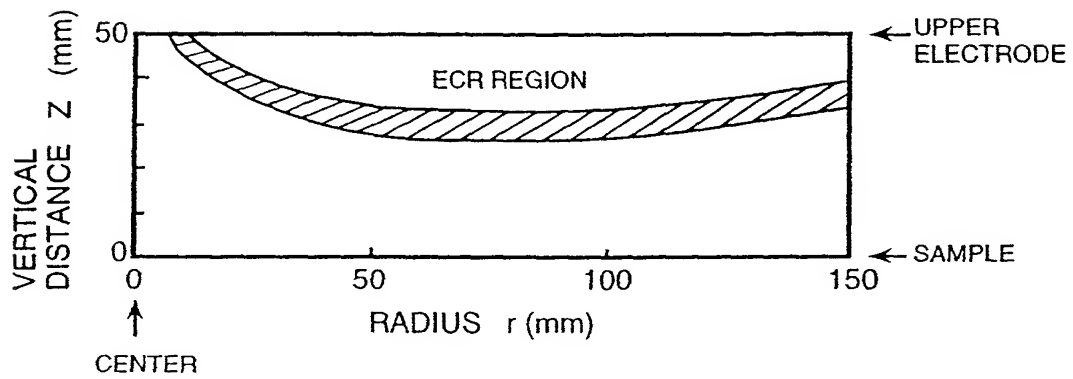


FIG.7(A)

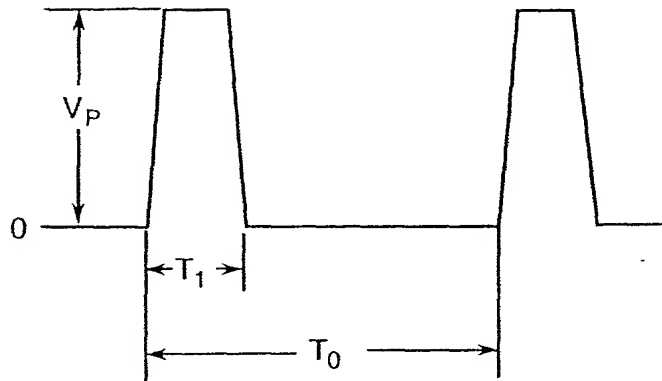
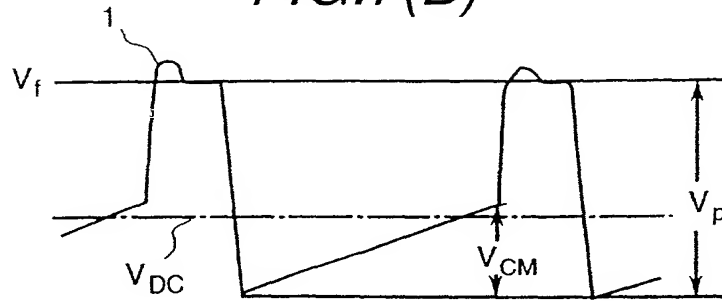


FIG.7(B)



$$V_{CM} = \frac{q}{c} = \frac{i_i \cdot (T_0 - T_1)}{(\epsilon_\gamma \epsilon_0 / d) \times K}$$

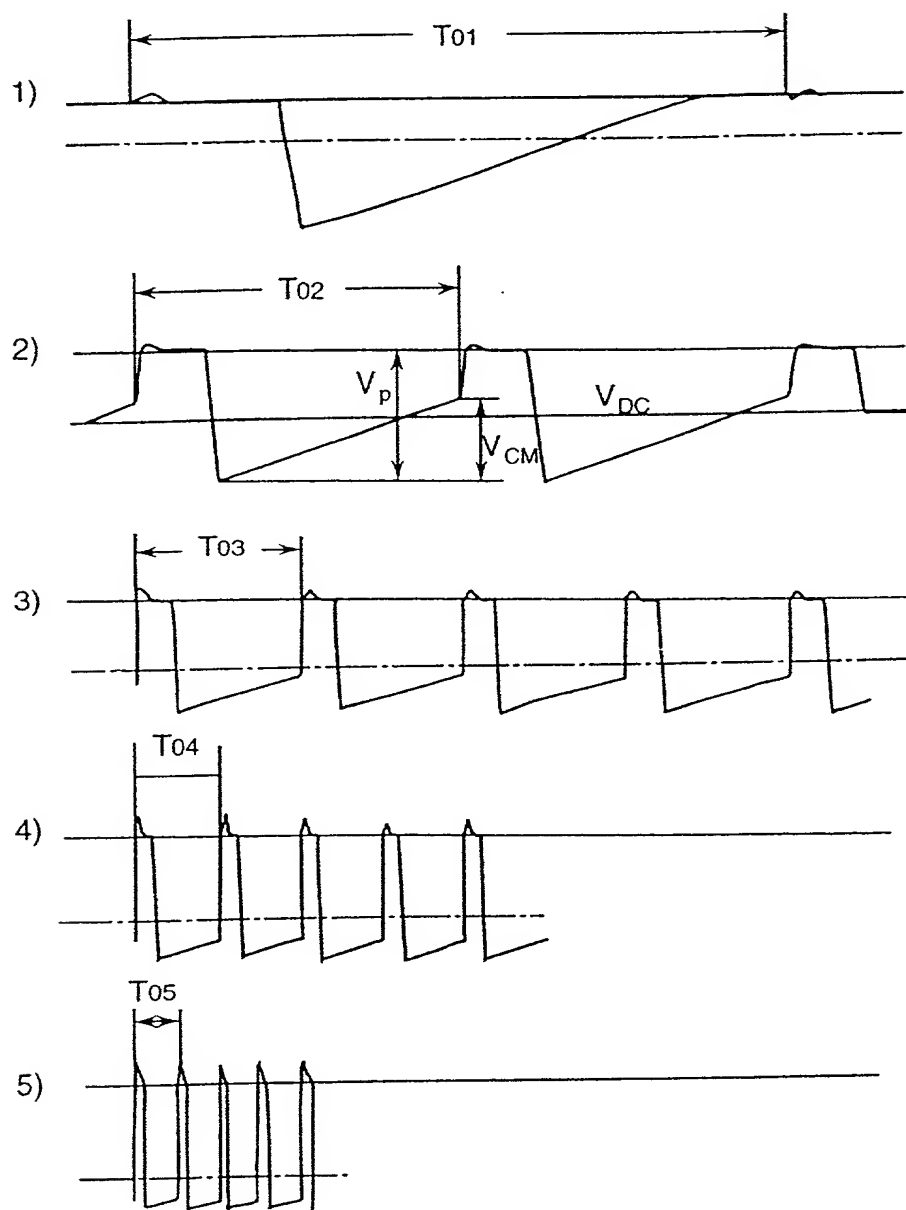
i_i : ION CURRENT DENSITY

ϵ_γ : SPECIFIC DIELECTRIC CONSTANT OF
ELECTROSTATIC ATTRACTING FILM

d : THICKNESS OF ELECTROSTATIC
ATTRACTING FILM

K : ELECTRODE COVERING RATIO OF
ELECTROSTATIC ATTRACTING FILM

FIG. 8



$$T_{01} : T_{02} : T_{03} : T_{04} : T_{05} = 16 : 8 : 4 : 2 : 1$$

FIG. 9

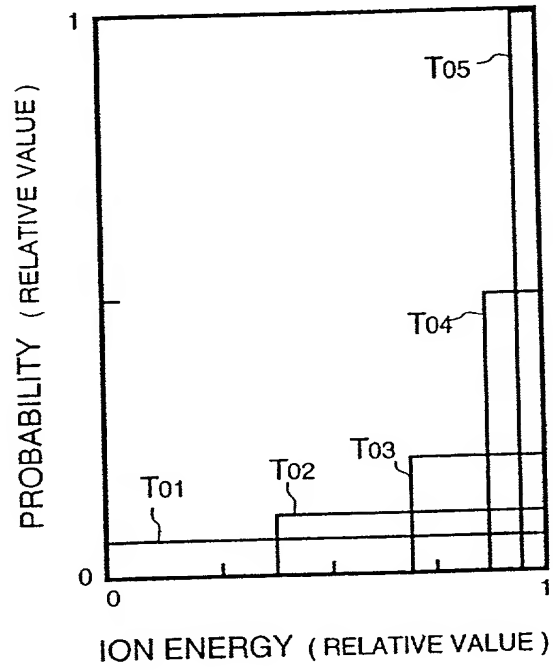


FIG. 10

$$V_{CM} = \frac{q}{c} = \frac{i_{io} \cdot (T_0 - T_1)}{(\epsilon_r \epsilon_o / d) \times K}$$

REFERENCE
CONDITION

$$\left\{ \begin{array}{l} i_{io} = 5 \text{ mA/cm}^2 \\ \epsilon_r = 10 \\ d_o = 0.3 \text{ mm} \\ K_o = 0.5 \end{array} \right.$$

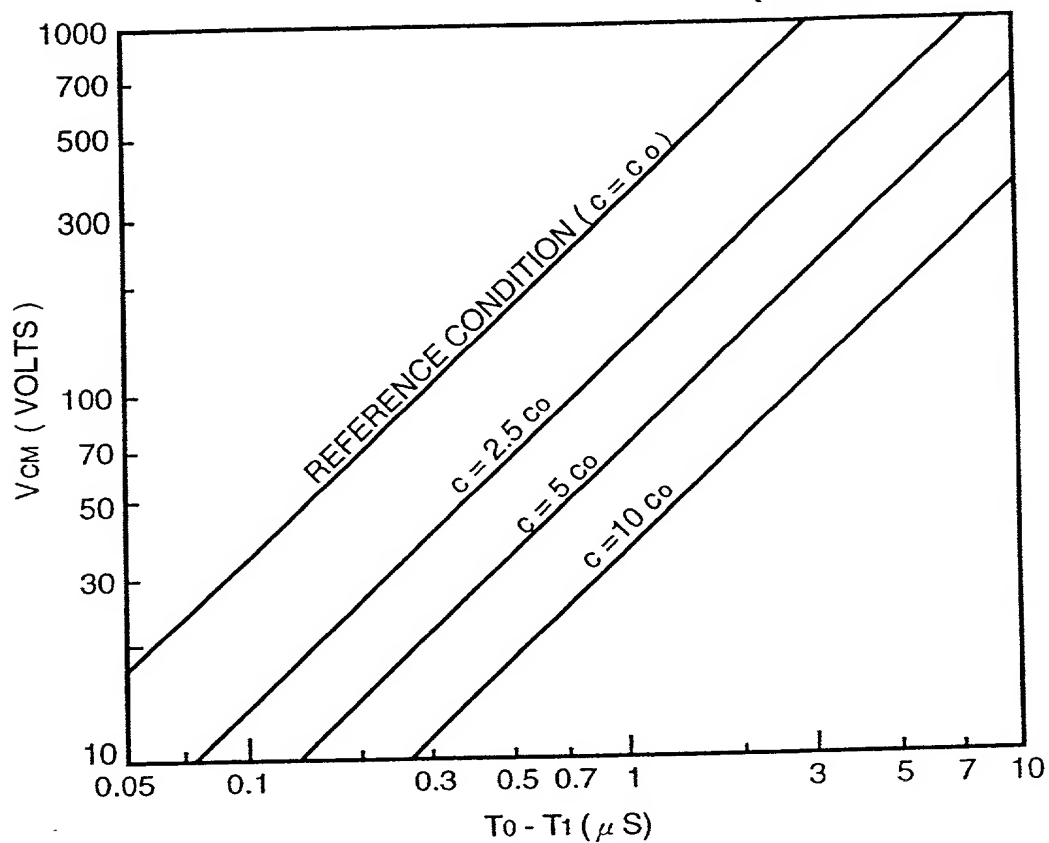


FIG. 11

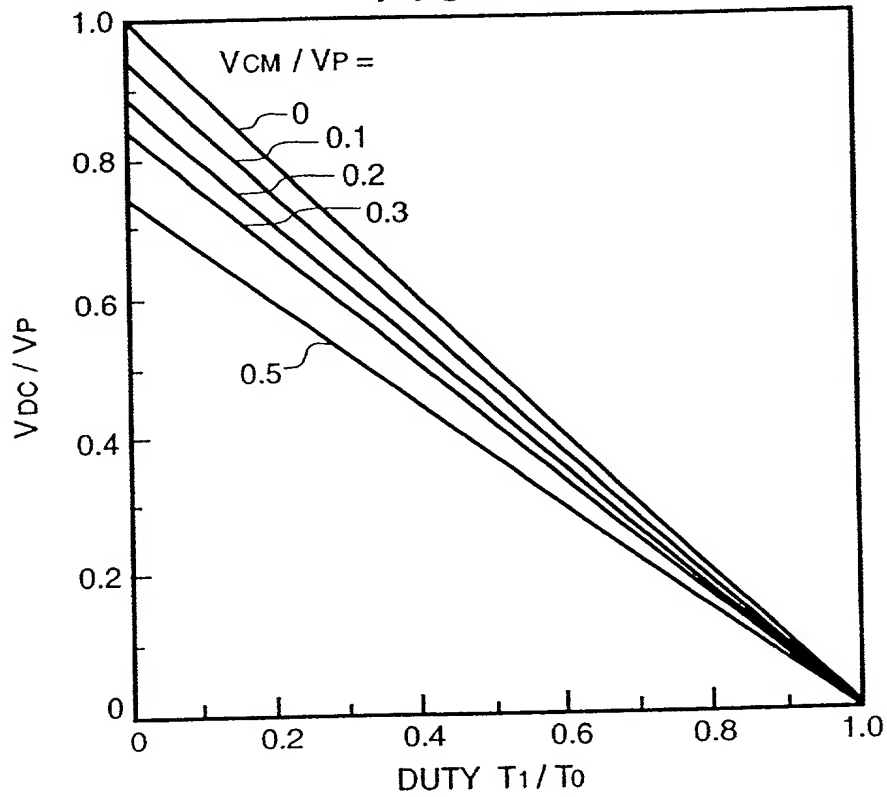


FIG. 12

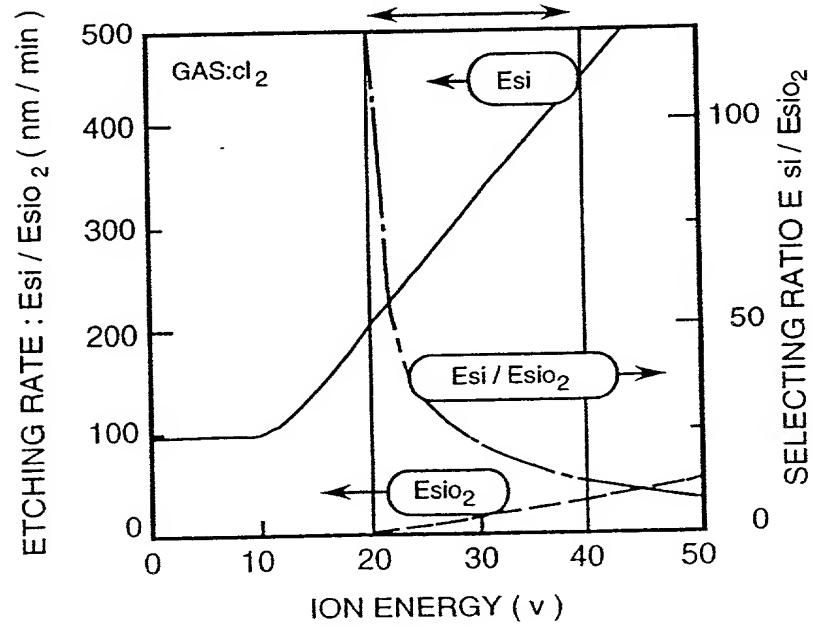
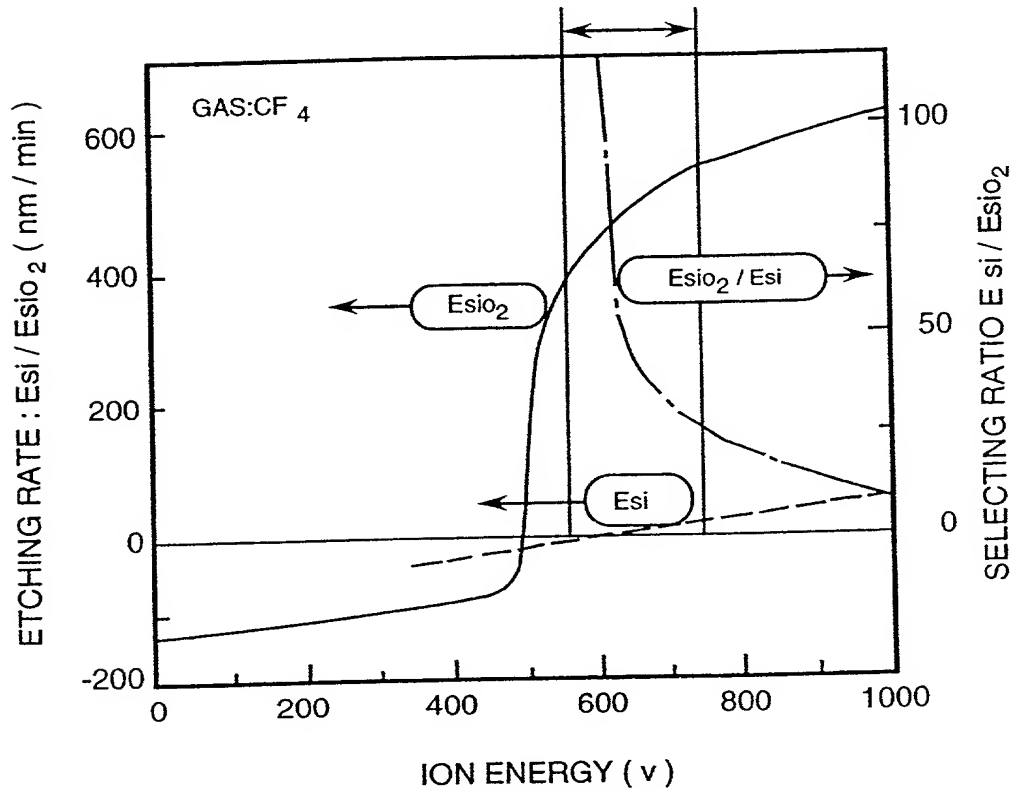


FIG. 13



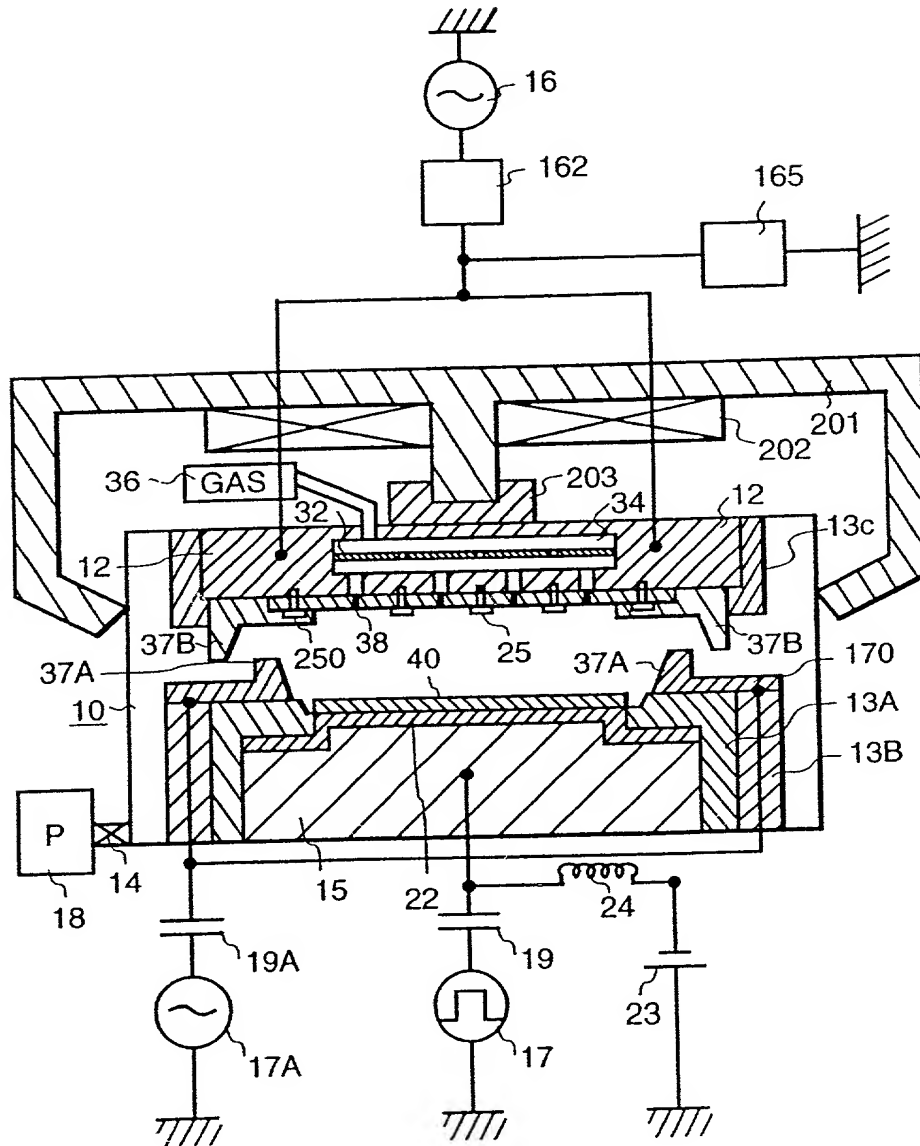
[illegible]

FIG. 15

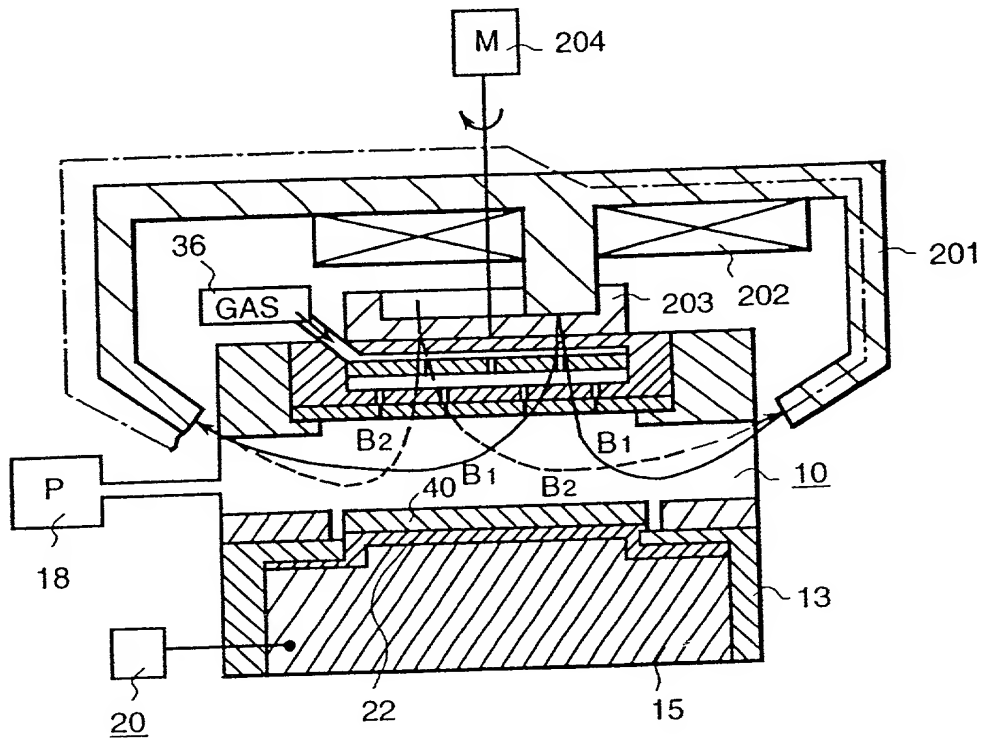


FIG. 16

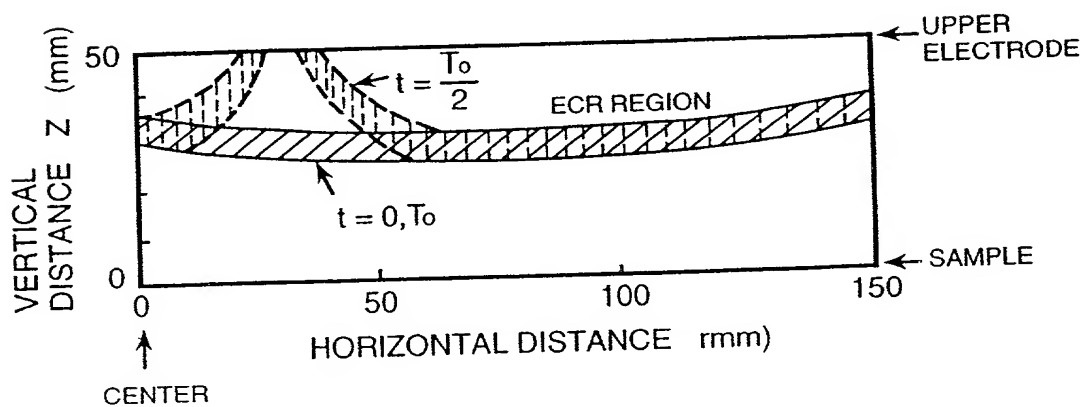


FIG. 17

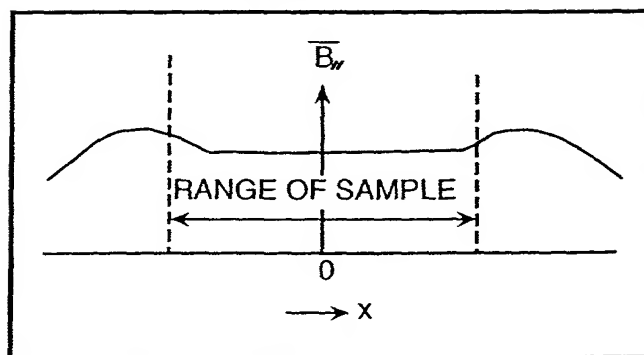


FIG. 18

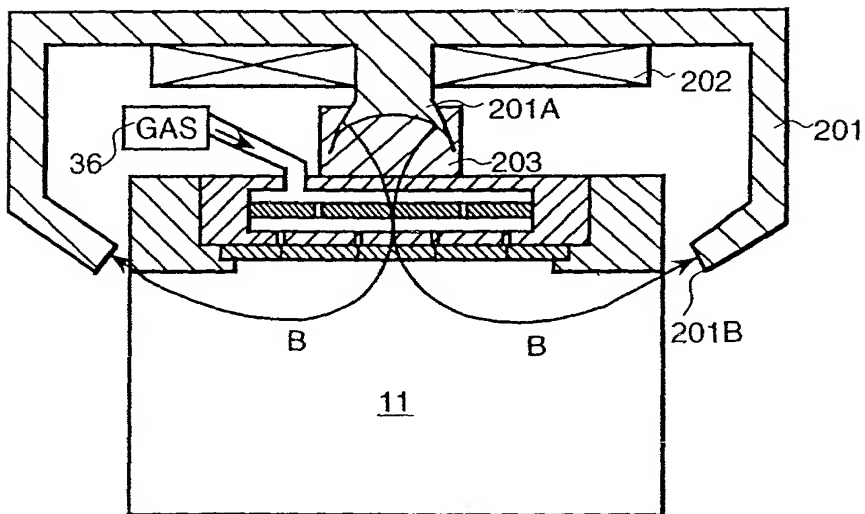


FIG. 19

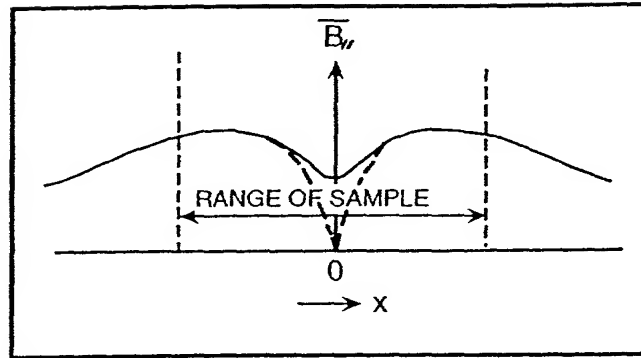


FIG. 20

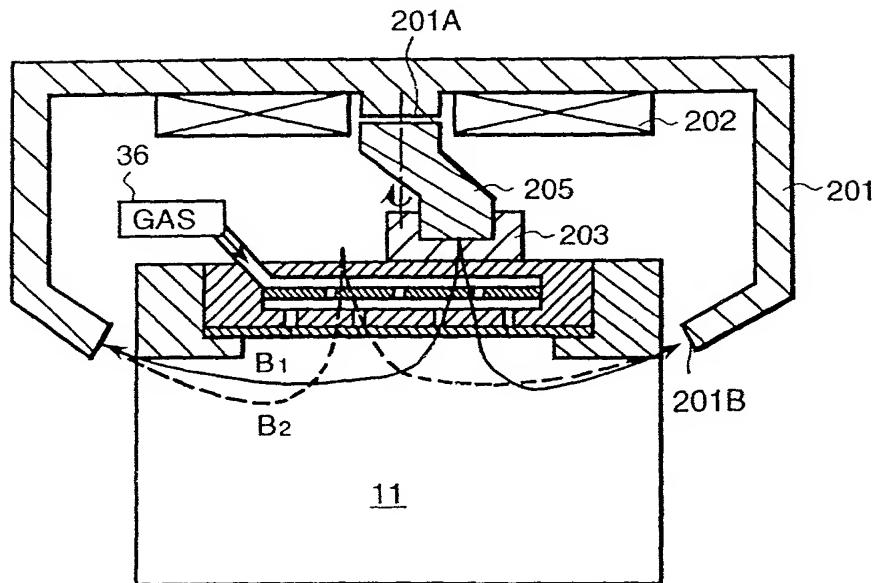


FIG. 21

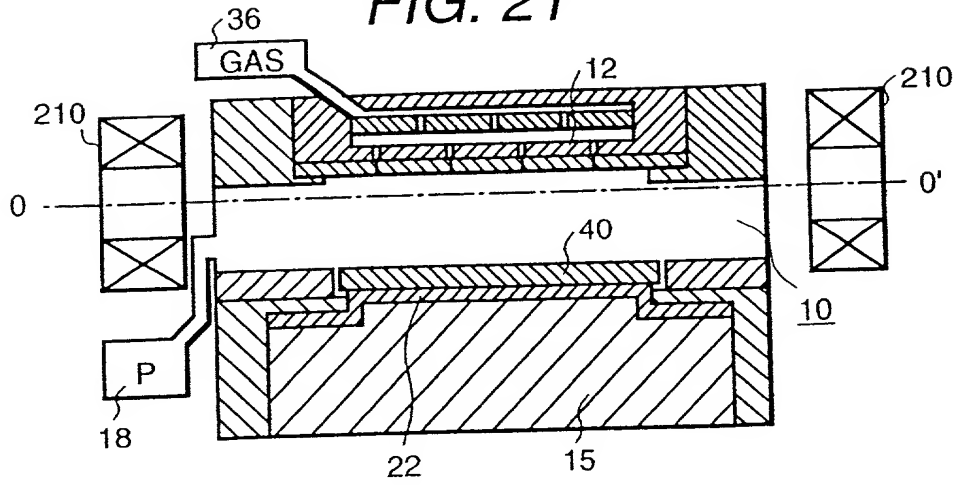


FIG. 22

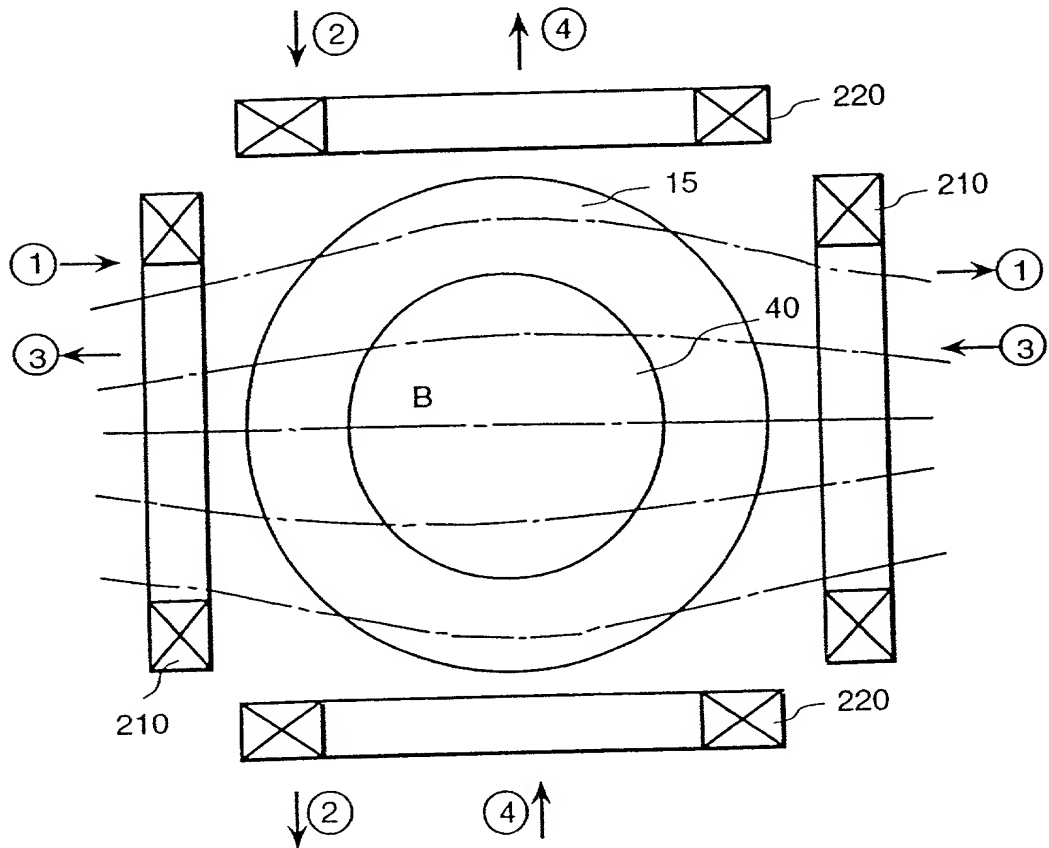


FIG. 23

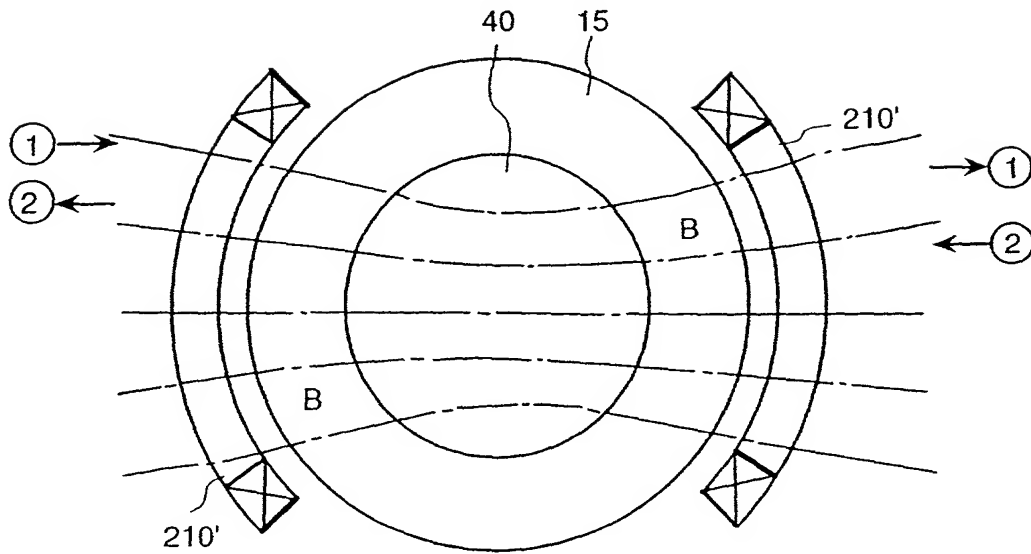


FIG. 24

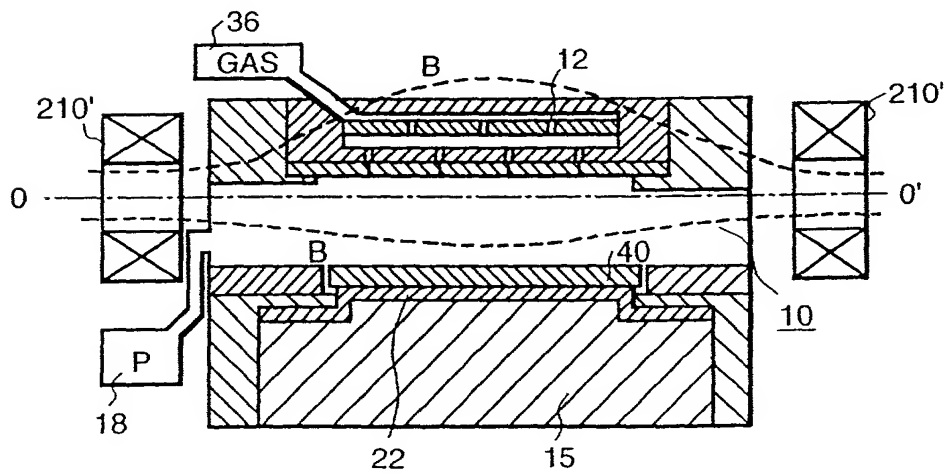


FIG. 25

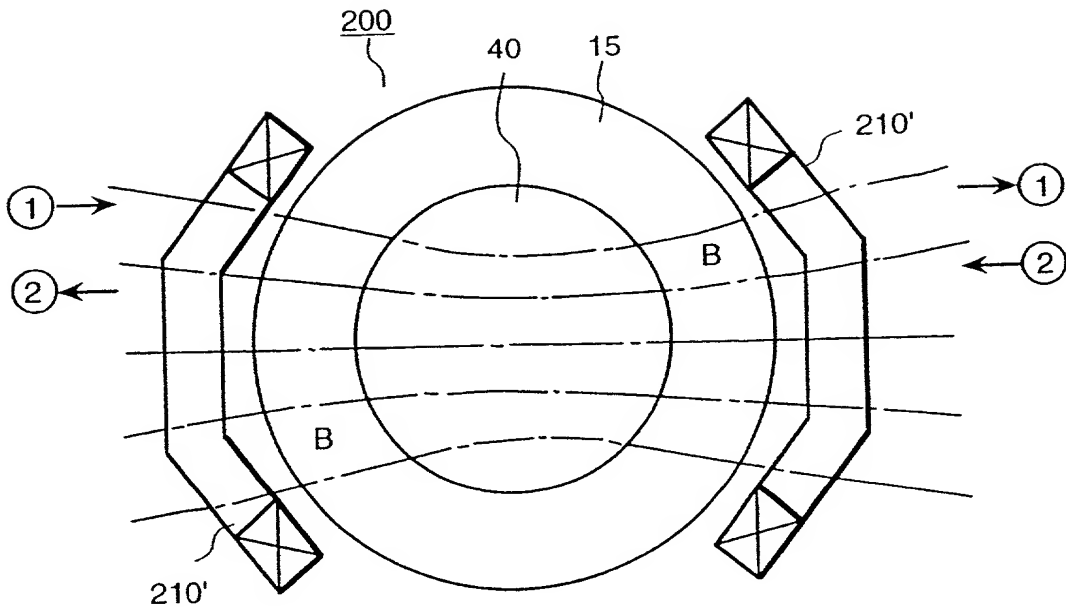


FIG. 26

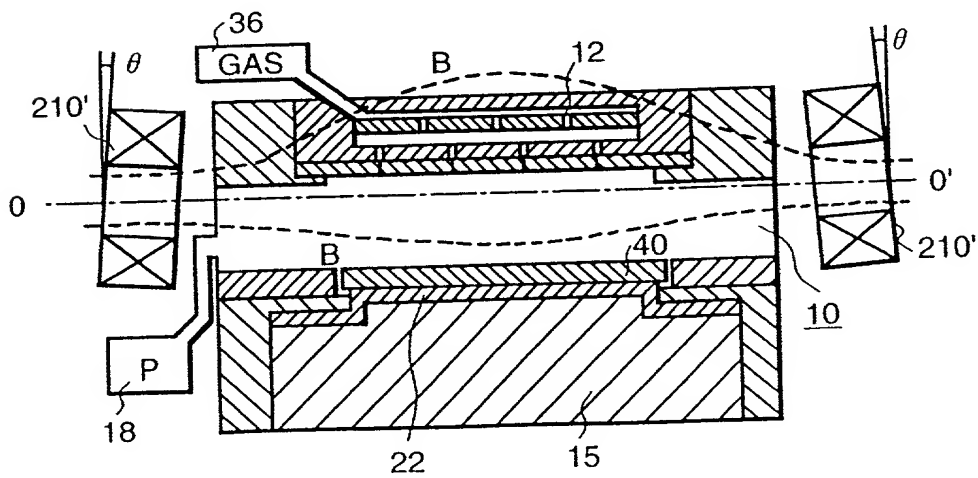


FIG. 27

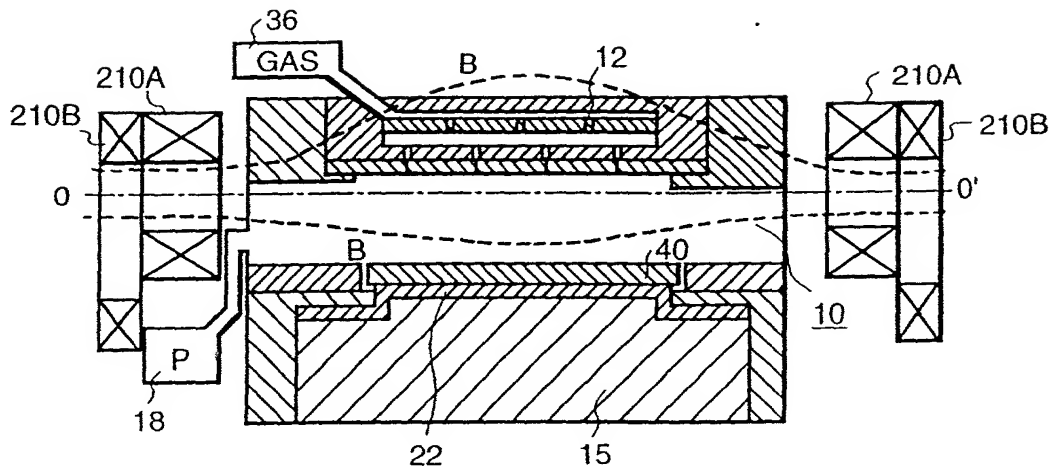


FIG. 28

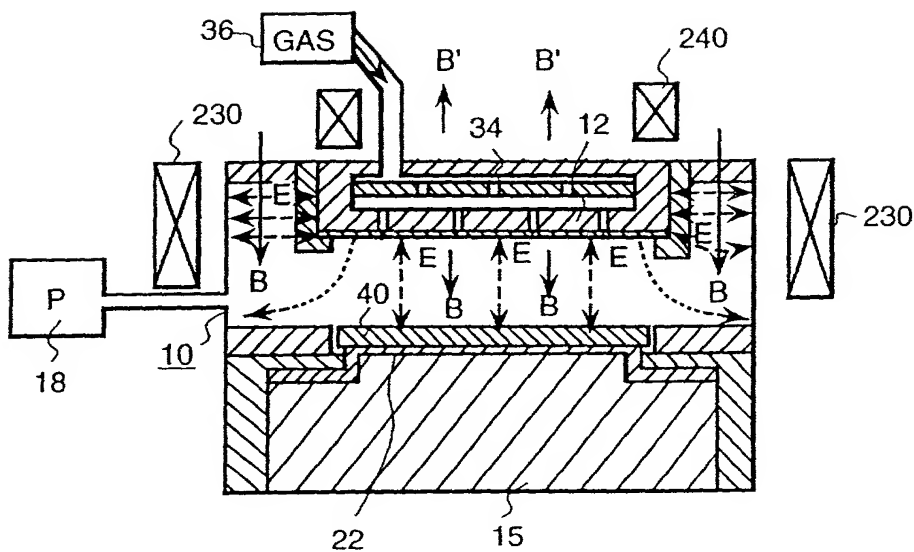


FIG. 29

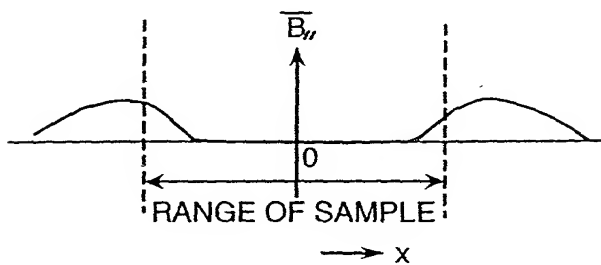


FIG. 30

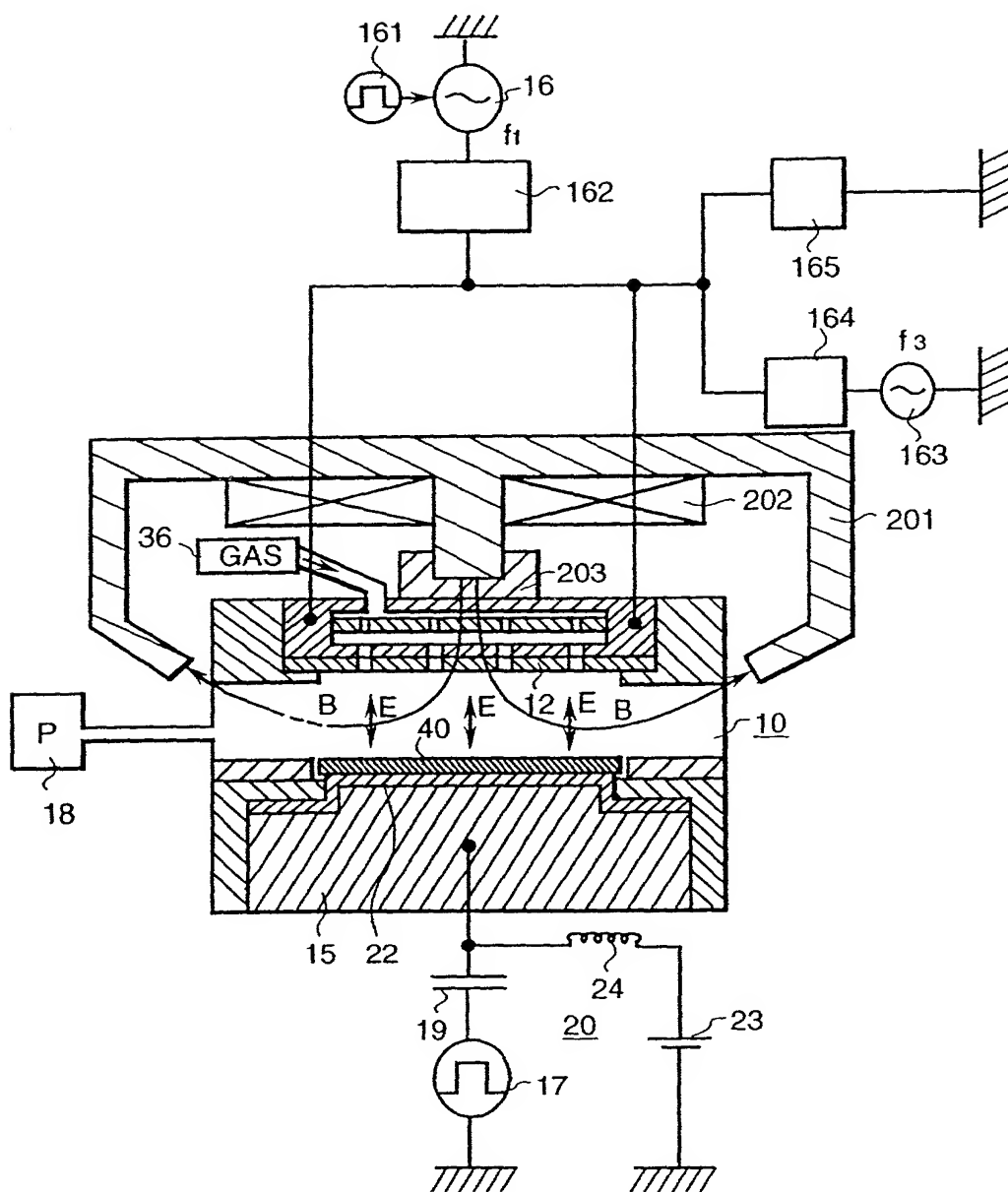


FIG. 31

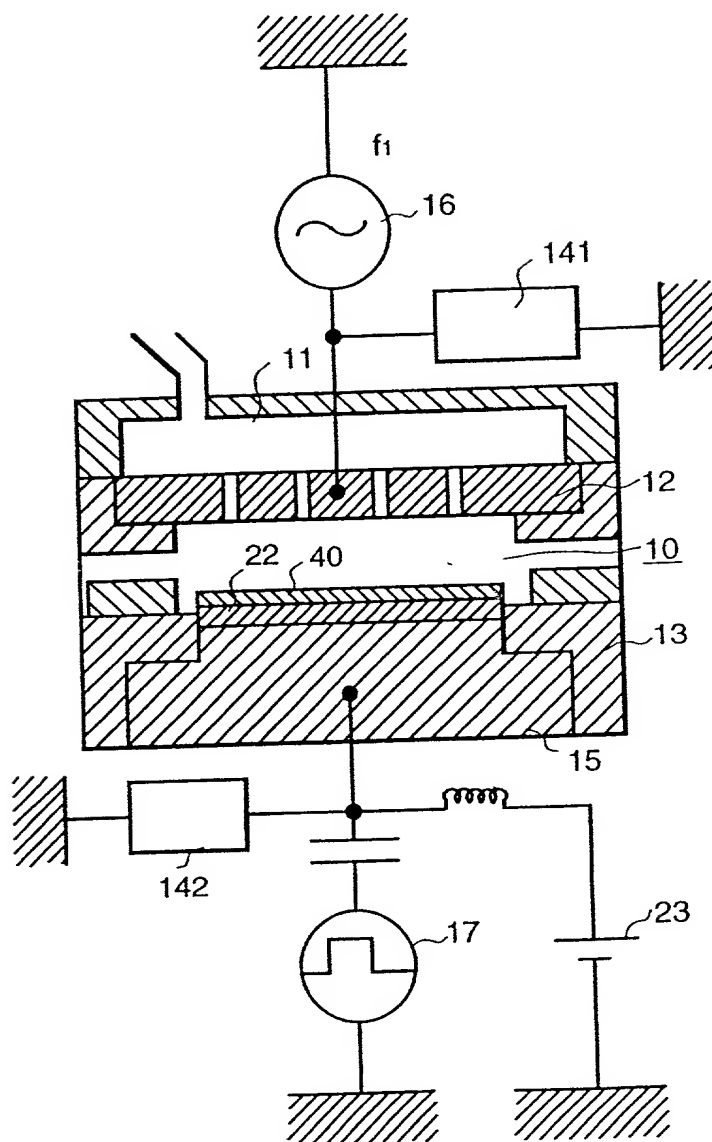
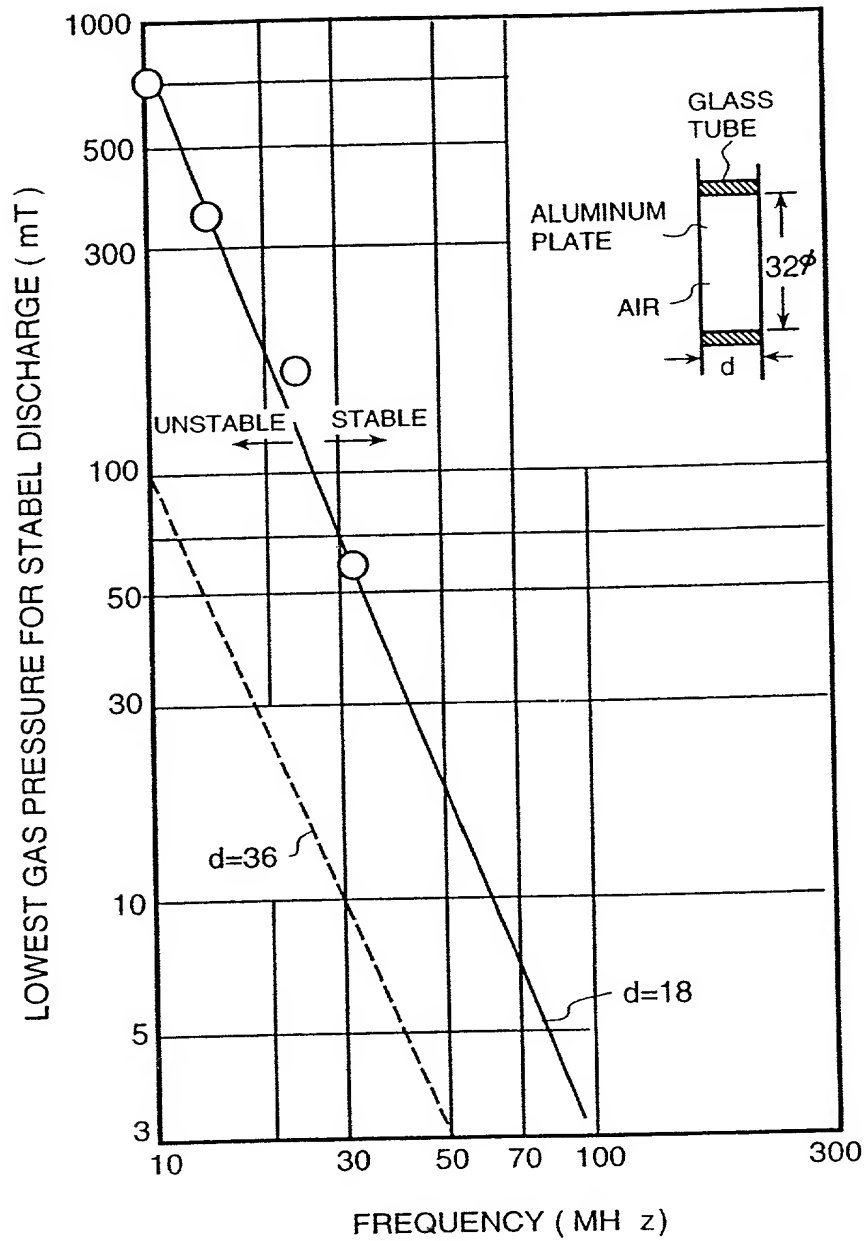


FIG. 32



FREQUENCY-LOWEST GAS PRESSURE FOR
STABLE DISCHARGE CHARACTERISTIC

FIG. 33

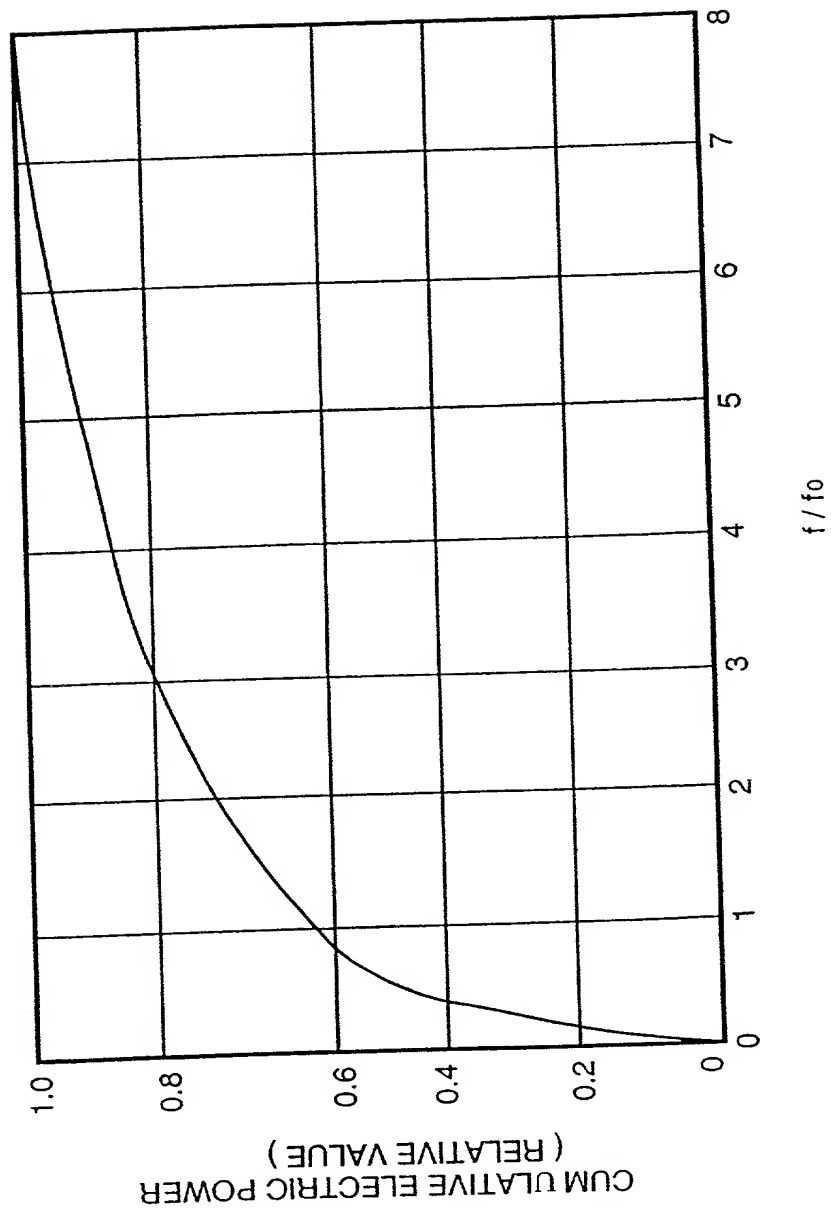


FIG. 34

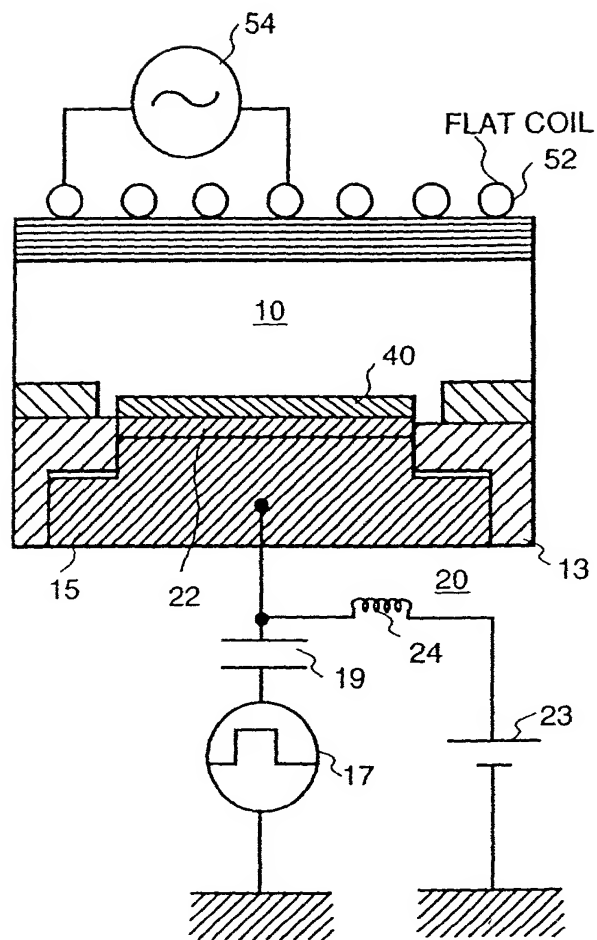


FIG. 35

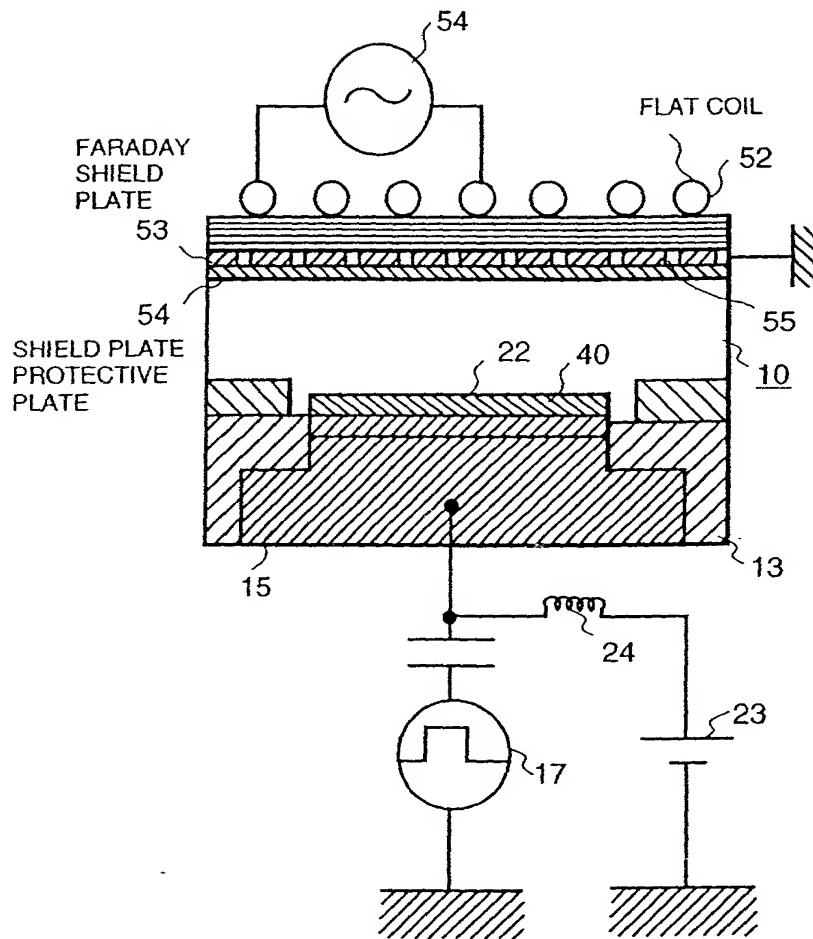


FIG. 36

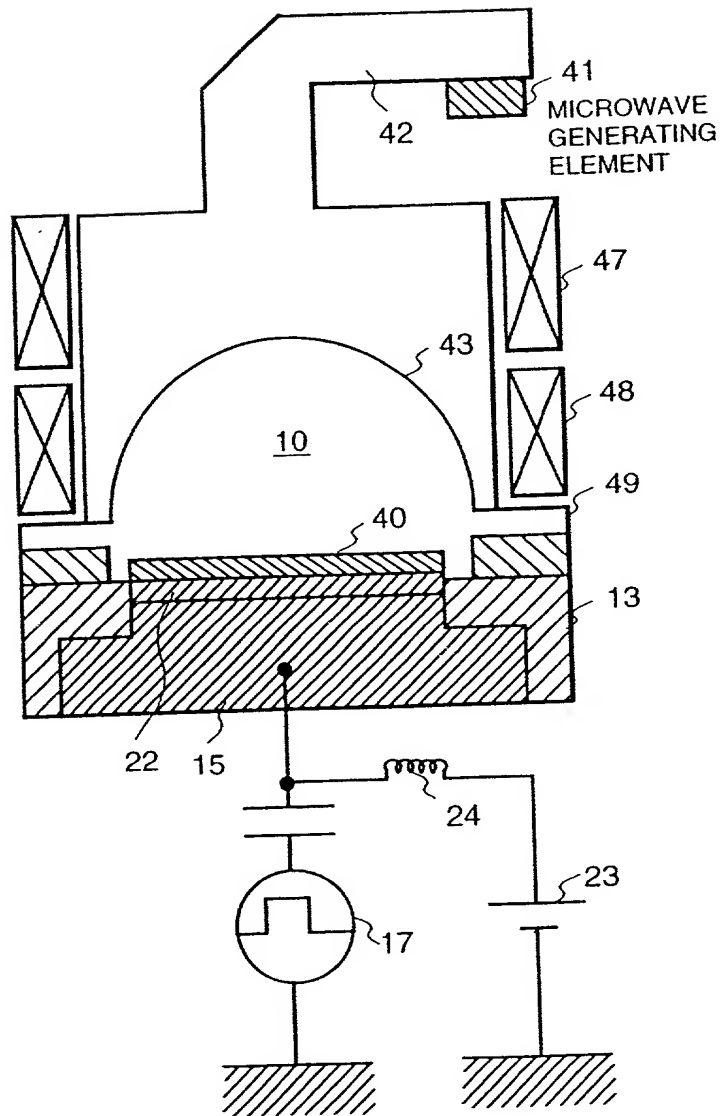


FIG. 37

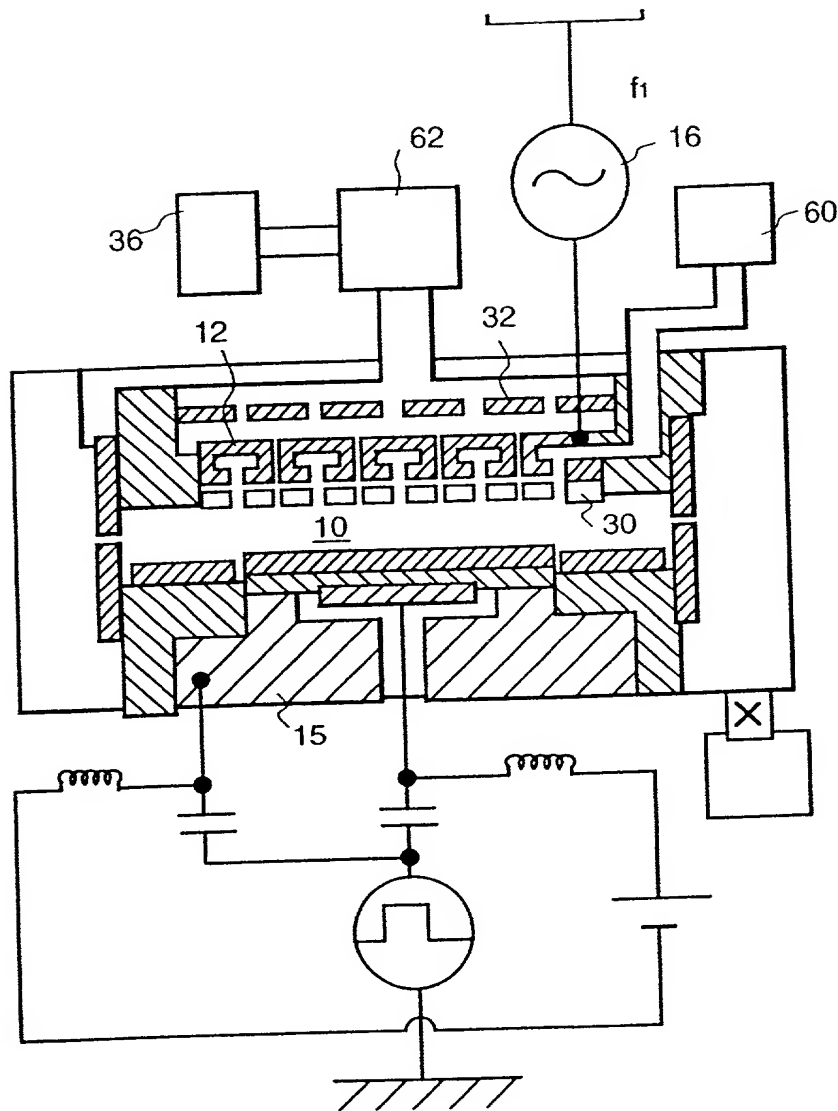


FIG. 39

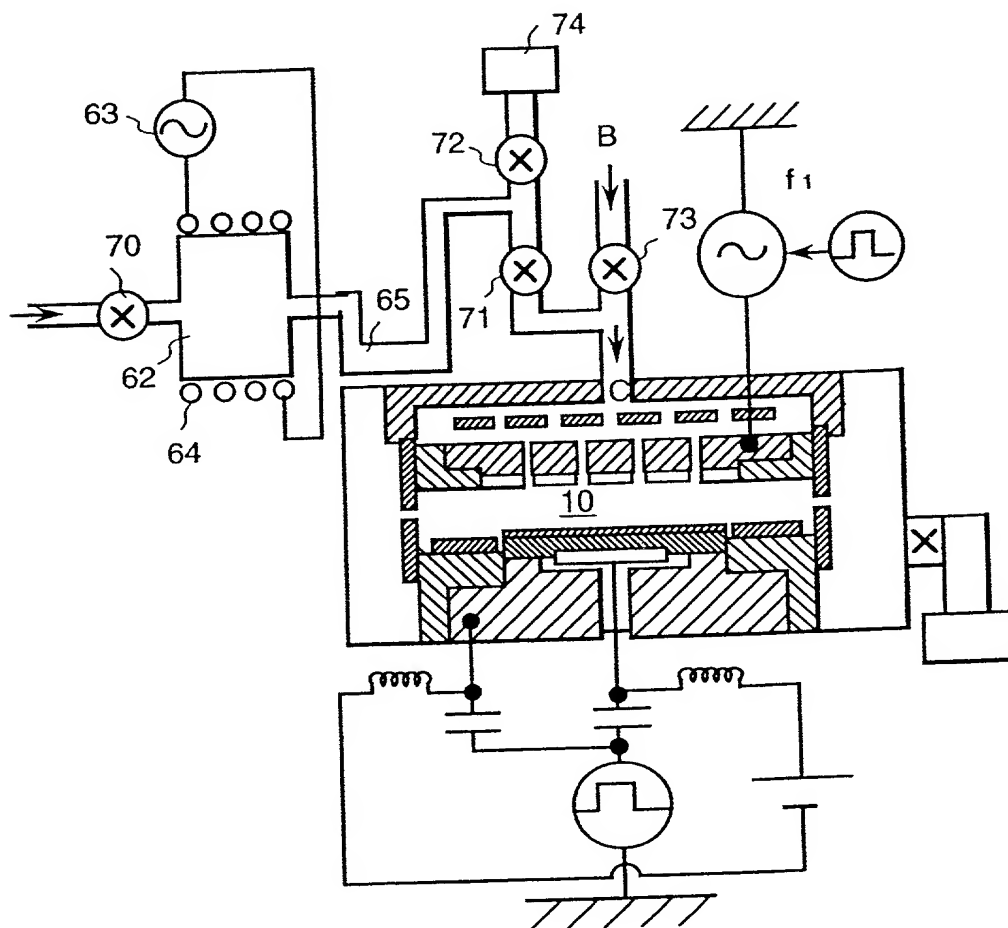


FIG. 40

